

Coulomb gap and variable range hopping in a pinned Wigner crystal

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(Dated: April 14, 2024)

It is shown that pinning of the electron Wigner crystal by a small concentration of charged impurities creates the finite density of charged localized states near the Fermi level. In the case of residual impurities in the spacer this density of states is related to nonlinear screening of a close acceptor by a Wigner crystal vacancy. On the other hand, intentional doping by a remote layer of donors is a source of a long range potential, which generates dislocations in Wigner crystal. Dislocations in turn create charged localized states near the Fermi level. In both cases Coulomb interaction of localized states leads to the soft Coulomb gap and ES variable range hopping at low enough temperatures.

The growth of GaAs heterostructures mobilities has made possible to study collective properties of the hole gas with a very small concentration. The average distance between holes r_s , calculated in units of the hole Bohr radius, has reached 80 and exceeded the theoretically predicted freezing point of the hole liquid, $r_s = 38$, where it should become the Wigner crystal. The transport of such low density system with and without magnetic field was studied recently. If a strong magnetic field applied along the hole plane the low temperature conductivity of the Wigner-crystal-like phase seems to be related to the variable range hopping (VRH)¹. Thus, it seems timely to discuss ohmic transport of the Wigner crystal. Of course, any Wigner crystal is always pinned by impurities and can not slide as a whole in a small electric field. Interstitials and vacancies of the Wigner crystal provide conductivity but they have large activation energies and freeze out at low temperatures. On the other hand, the VRH conductivity requires nonzero density of states of charge excitations near the Fermi level, both in the case of Mott law or Efros-Shklovskii (ES) law. If pinning centers produce such "bare" density of states then the long range Coulomb interaction creates the Coulomb gap around the Fermi level and leads to the ES variable range hopping. In this paper, I study the origin of the bare density of states of the pinned Wigner crystal, the Coulomb gap on its background and the resulting VRH conductivity at low temperatures.

Let me start from a clean electron Wigner crystal on uniform positive background. Consider an additional electron added to the perfect Wigner crystal and let the lattice relax locally. This addition costs the interstitial energy $0.14e^2/a$, where a is the lattice constant or the optimal triangular lattice, ϵ is the dielectric constant of GaAs². On the other hand, the energy cost of the extraction of an electron and the corresponding relaxation around the vacancy is equal to the vacancy energy $0.26e^2/a$. Thus, the density of states of relaxed excitations (electronic polarons³), consists of two delta-like peaks at energies $0.26e^2/a$ and $0.14e^2/a$. The lower peak corresponds to occupied states, the upper one contains empty states. Between them there is the hard (completely empty) gap of the width $0.40e^2/a$. The Fermi level of electronic polarons (the zero of energy) is situated

in this gap, therefore the density of states at the Fermi level is zero.

In typical samples the Wigner crystal is pinned by charged impurities: donor and acceptors. Even if there is no intentional doping and the two-dimensional electrons gas (2DEG) is created in a heterostructure by a distant metallic gate, there is always a small concentration of residual donors and acceptors. Many high mobility heterostructures are intentionally doped by a donor layer, which is separated from 2DEG by the spacer with a large width s . This is an additional source of disorder. In the beginning of this paper we neglect this source and deal with residual impurities only. We return to the role of doped layer in the second part of this paper.

Let me argue that close residual donors and acceptors create localized states at the Fermi level. I use theory of pinning of the Wigner crystal by charge impurities developed in Ref. 4. As in that paper I talk about Wigner crystal of electrons and concentrate on close residual acceptors which according to Ref. 4 produce stronger pinning than donors. (For the hole crystal the role of acceptors is of course played by donors.) Because the spacer width, s , and the lattice constant of the Wigner crystal, a , are much larger than the lattice constant of AlGaAs the authors of Ref. 4 assumed that acceptors are randomly distributed in space with three-dimensional concentration N . Each acceptor is negative because it has captured one electron from 2DEG.

It was found⁴ that effect of an acceptor dramatically depends on its distance, d , from the plane of the Wigner crystal. If d is larger than $0.68a$ the electron crystal adjusts to acceptor in such a way that in the ground state an interstitial position of the crystal is exactly above the acceptor. In this case, interaction of the acceptor with the Wigner crystal can be calculated in the elastic approximation. On the other hand, when d is smaller than $0.68a$ acceptor creates a vacancy in the crystal, which positions itself right above the acceptor. This means that the close acceptor effectively builds in the crystal site pushing away to infinity its electron. We can consider the latter acceptor as an empty localized state for electron, while the former acceptor can be considered as a localized state occupied by an electron. Their energies are equal at $d = 0.68a$, so that all acceptors with $d > 0.68a$

are occupied and all acceptor with $d < 0.68a$ are empty. Thus, acceptors with $d = 0.68a$ are at the Fermi level and the bare density of states near the Fermi level

$$g_B = \frac{N a}{e^2 a}; \quad (1)$$

where $N a$ is an estimate of the two-dimensional concentration of acceptors located within distance a (only they provide substantial pinning) and e^2/a is the characteristic energy of their pinning. The nonzero density of states g_B makes possible VRH conductivity of the pinned Wigner crystal. For example, an electron from an acceptor with $d = 0.68a + 0$ can hop to a distant one with $d = 0.68a - 0$.

The long range Coulomb interaction between localized states leads to the soft Coulomb gap at the Fermi level⁵. Shape of the Coulomb gap depends on the interaction, $U(r)$, of the hopping electron in the final state of the hop and the empty place it has left behind (excitonic term)^{3,5}. If the interaction can be described by the standard Coulomb law $U_C(r) = e^2/r$, where r is the two-dimensional distance between initial and final state, then the Coulomb gap has the standard form for two-dimensional case

$$g(E) = \frac{2 E_j^2}{e^4}; \quad (2)$$

The attraction potential $U(r)$ generally speaking is different from $U_C(r)$ due to screening of the Coulomb interaction by elastic deformations of the Wigner crystal or in other words by its polarization. In order to calculate Fourier image $U(q)$ of $U(r)$ we have to introduce the Larkin length L at which acceptors destroy the long range order of the crystal. In the two-dimensional Wigner crystal pinning by close acceptors is so strong that this length is close to the average distance between them, $L \approx (N a)^{-1/2}$. Using L , we can write

$$U(q) = 2 \pi q^{-1}(q); \quad (3)$$

where

$$(q) = 1 + \frac{2}{q r_D} \frac{q^2}{q^2 L^{-2}}; \quad (4)$$

is given by interpolation between large and small q cases. Here $r_D = 0.32a$ is the linear Debye screening radius of the Wigner crystal. (The asymptotics of Eq. (4) at large and small q are similar to those of the dielectric constant of a two-dimensional electron gas in a strong magnetic field^{7,8}, where the Larmor radius plays the role of L .)

In the real space the Fourier image of Eq. (4) results in the Coulomb potential $U(r) = U_C(r)$ only at $r \gg L^2 a = 1/N a^2$. One can say that by these distances all electric lines of a probe charge located in the reference point in the plane of Wigner crystal leave the plane. This leads to the standard Coulomb gap Eq. (2), but only at energies $E_j < e^2 N a^2$. At smaller distances r

$1/N a^2$ potential $U(r)$ is weaker than $U_C(r)$ and grows only logarithmically with decreasing r . But this does not lead to faster (exponential) growth of the density of states at $E_j \approx e^2 N a^2$ as it would if g_B were very large. The reason is that at energy $E_j \approx e^2 N a^2$ the Coulomb gap density of states, Eq. (2), already reaches the bare density of states, g_B , given by Eq. (1). The Coulomb gap is just a depletion of the density of states on the background of the bare density. Therefore, the density of states in the Coulomb gap can not be larger than g_B ³. This means that at $E_j \approx e^2 N a^2$ the density of states saturates at the level of Eq. (1).

The role of distance $L^2 a = 1/N a^2$ can be interpreted in another way. When we add an electron to the clean Wigner crystal it makes an interstitial but its charge spreads to infinity. In the pinned Wigner crystal an added charge is smeared in the disc of the finite radius R . We can find R minimizing the sum of the Coulomb energy $e^2 = R$ of the disc of radius r and the shear energy $(u=L)^2 r^2$ necessary for the disc dilatation by the area a^2 . Here e^2/a^3 is the shear modulus and $u = a^2/r$ is the necessary displacement. It is important that the characteristic distance of the variation of the shear displacement (which percolates between strongly pinning acceptors) $L \approx (N a)^{-1/2}$. Minimizing this sum we find that $R = L^2 a = 1/N a^2$. This again tells us that at distances larger than $L^2 a = 1/N a^2$ we deal with the unscreened Coulomb potential.

At low enough temperatures the Coulomb gap leads to Efros-Shklovskii (ES) law of the temperature dependence of the variable range hopping^{3,5}

$$= \sigma_0 \exp [-(T_{ES} = T)^{1/2}]; \quad (5)$$

Here σ_0 is a prefactor, which has only an algebraic T -dependence and

$$T_{ES} = C e^2; \quad (6)$$

where C is a numerical coefficient close to 6 and ℓ is the localization length for electron tunnelling with energy close to the Fermi level in the Wigner crystal. We will discuss the value of ℓ in the end of the paper.

When with increasing temperature the width of the band of energies used for ES hopping $(T/T_{ES})^{1/2}$ reaches $e^2 N a^2$ ES law is replaced by the Mott conductivity

$$= \sigma_0 \exp [-(T_M = T)^{1/3}]; \quad (7)$$

where $T_M = C_M (g_B^{-2})$. Transition from the ES law to the Mott law happens at $T = T_{ES}^3 = T_M^2 = T_{ES} (N a^2)^2$. Thus, while ES law does not depend on the acceptor concentration N the range of ES law shrinks when concentration of acceptors decreases.

This example emphasizes universality of the Coulomb gap and ES law. The Coulomb gap was derived for lightly doped semiconductors, where disorder is as strong as interactions⁵. Later Efros⁹ suggested a model, where electrons are located on sites of a square lattice with $+1/2$

charges, the number of sites being twice larger than number of electrons. Random energies of sites are uniformly distributed in the band A (they are measured in units of Coulomb interaction of two electrons on nearest sites). In this model the Coulomb gap does not survive in the small disorder case $A \ll 1$ because in this case in spite of small disorder positive charges of empty sites and negative charges of occupied sites alternate in the perfect NaCl-like order. One could, therefore, say that the Coulomb gap is the property of strong disorder only. The above example of the Wigner crystal on the uniform background pinned by rare strong impurities however shows that such impression may be misleading. Even in the case when concentration of acceptors N is small (one can call it the weak disorder case) the Coulomb gap and ES law survive.

One can interpret what happens with the Wigner crystal in the terms of the Efros model. At strong disorder when $N a^3 \ll 1$ our model is close to the Efros model with $A \ll 1$. When parameter $N a^3$ becomes much smaller than unity and the disorder becomes weak, the energy scatter of states created by impurities stays at the level of e^2/a , while the long Coulomb interaction between these states becomes much smaller, of the order of $e^2 (N a^3)^{1/2} \kappa$. Introducing a two-dimensional random lattice with sites occupied by acceptors we can come to a renormalized Efros model with $A \ll 1 = (N a^3)^{1/2} \kappa$. This brings us again to the Coulomb gap at small energies.

Until now we talked about the role of residual acceptors. Let us qualitatively discuss intentionally doped heterojunctions where donors are situated in the narrow layer parallel to the plane of the 2DEG (delta-doping) at a large distance s from 2DEG. Random distribution of donors in this layer creates fluctuations of their potential of all wavelengths, but only harmonics of the random potential with wavelengths larger than s reach 2DEG. Let us assume that the two-dimensional concentration of charged donors in the doped layer is N_2 . In principle N_2 can be different from the two-dimensional concentration of electrons in the Wigner crystal (2DEG can be compensated by acceptors or created by illumination). If $N_2 \ll n$ the Wigner crystal screens external potential by small, purely elastic deformations. Due to these deformations energies of an interstitial and a vacancy depend on coordinates. Therefore, both delta-like peaks of the density of states are somewhat smeared. Their width, however, is much smaller than the hard gap between them. Thus, the hard gap is preserved and no states at the Fermi level appear. When the concentration of donors, N_2 , grows, the amplitude u of displacements of electrons in the Wigner crystal with wavelength of the order s reaches the lattice constant of the crystal a . Such large deformations resolve themselves by creation of dislocations^{10,11}, because the energy price of the dislocation core becomes smaller than an elastic energy, which is eliminated by the dislocation. This happens when the donor concentration, N_2 , is of the order of electron concentration, n . Indeed, if we cover the layer of donors by

squares with the side s the typical fluctuation of number of charges in a square is equal $(N_2 s^2)^{1/2}$. Potential of the charge of this fluctuation reaches 2DEG practically without compensation by oppositely charged fluctuations in neighboring squares. As a result at $n = N_2$ 2DEG has to provide $(N_2 s^2)^{1/2} = s$ new electrons to screen random potential in a square. This may be done by an additional row of electrons in the square or, in other words, by two dislocations. Thus approximately one dislocation appears in a square with a side s . This picture is actually a simple visualization of the Larkin domain. Below we concentrate on the case $N_2 \ll n$. In this case, the length s plays the role of the Larkin length L .

An isolated dislocation brings the electronic polaron state right to the Fermi level. Indeed, if we add an electron from the Fermi level to the end of an additional row terminated by a dislocation and let the rest of electrons relax, the dislocation just moves along this additional row by one lattice constant a and the energy remains unchanged. Similarly, if we extract an electron from the end of the row to the Fermi level, the dislocation moves in the opposite direction and the energy does not change. This means that if we neglect the interaction of dislocation with long range potential of donors and interaction between dislocations they create a delta peak of the density of states right at the Fermi level. This peak is normalized on the concentration of dislocations. The Fermi level is pinned in the middle of this peak.

In the long range fluctuating potential of donors the peak of the density of dislocation states is smeared, because dislocations strongly interact with the gradient of potential. The peak is smeared also due to the interaction between the dislocations. When an additional electron is absorbed by a dislocation and, as a result, the dislocation moves by one lattice site, the logarithmic interaction with other dislocation changes.

To understand the role of Coulomb interaction in the density of states of the pinned Wigner crystal one has to concentrate on the fate of the charge of an added electron. In the clean Wigner crystal, if we have a single dislocation and move it by one lattice constant adding a new electron, the charge of this electron spreads to infinity, leaving the dislocation neutral.

If we have a gas of dislocations in the positions fixed by disorder and their interaction, a single charge can only spread to the finite distance, R . It can be estimated in the way we did for residual randomly distributed acceptors. If we assume that dislocations are fixed in space by fluctuating donor potential the extra electron charge spreads optimizing the sum of its Coulomb energy and the energy of the shear deformation. Optimization leads to $R \propto s$. Thus, the Coulomb potential of charges inside the pinned Wigner crystal is valid at distances in the plane $r \propto s$.

This system is clearly similar to the Coulomb glass and therefore has the Coulomb gap. Indeed, as we mentioned above the derivation of the Coulomb gap is based upon the observation that when a localized electron is

transferred to another localized state one should take into account its $1/r$ Coulomb attraction with the hole it has left (the excitonic effect). We claimed above that that the Coulomb interaction is valid if $r \ll a$. Therefore, the linear in energy Coulomb gap appears at the Fermi level. The width of this gap is $e^2/R = e^2/a$. At $a \ll r$ the Coulomb gap occupies only a small fraction of the energy range between interstitial and vacancy peaks. Away from the Coulomb gap the density of states is almost constant. Thus, in the case of intentional n -doping by remote donors we again arrive to the Coulomb gap of density of states and correspondingly to ES law at low temperatures.

Let us discuss the value of localization length in Eq. (6). In classical Wigner crystal $a = \frac{1}{k_F} = \frac{1}{k_F^2}$. This is a quite small value which leads to too large T_0 and very large resistances in the range of ES law. However, close to the melting point of the Wigner crystal a can be

much larger, making an observation of ES law in pinned Wigner crystal more realistic. Magnetoresistance, observed in Ref. 1 may be related to ES variable range hopping conductivity.

In conclusion, I emphasize again that I am dealing with the Wigner crystal which in the absence of impurities slides on the positive background. Impurities pin this Wigner crystal and lead to ES VRH conductivity due to hops between its pieces. This situation is similar to what happens in a system of many quantum dots situated in random electrostatic potential of stray charges or in a system of many electron puddles with random positive charge of their background. Similar physics was recently theoretically studied in quasi-one-dimensional systems¹².

I am grateful to M. M. Fogler, A. L. Efros and S. Teber for many important discussions. This paper is supported by NSF DMR-9985785.

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